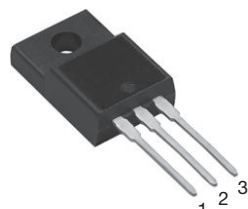
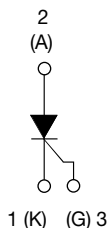




Thyristor High Voltage, Phase Control SCR, 25 A



TO-220AB FULL-PAK



FEATURES

- Designed and qualified for industrial level
- Fully isolated package ($V_{INS} = 2500 V_{RMS}$)
- UL E78996 approved
- 125 °C max. operating junction temperature
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-25TTS...FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRODUCT SUMMARY

Package	TO-220AB FP
Diode variation	Single SCR
$I_{T(AV)}$	16 A
V_{DRM}/V_{RRM}	800 V, 1200 V
V_{TM}	1.25 V
I_{GT}	45 mA
T_J	-40 °C to 125 °C

OUTPUT CURRENT IN TYPICAL APPLICATIONS

APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	18	22	A

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	16	A
I_{RMS}		25	
V_{RRM}/V_{DRM}		800/1200	V
I_{TSM}		350	A
V_T	16 A, $T_J = 25$ °C	1.25	V
dV/dt		500	V/ μ s
dI/dt		150	A/ μ s
T_J		-40 to 125	°C

VOLTAGE RATINGS

PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VS-25TTS08FPPbF, VS-25TTS08FP-M3	800	800	10
VS-25TTS12FPPbF, VS-25TTS12FP-M3	1200	1200	



ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			TYP.	MAX.	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 51\text{ }^{\circ}\text{C}$, 180° conduction half sine wave	16		A
Maximum RMS on-state current	I_{RMS}		25		
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	300		
		10 ms sine pulse, no voltage reapplied	350		
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	450		A^2s
		10 ms sine pulse, no voltage reapplied	630		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to } 10\text{ ms}$, no voltage reapplied	6300		$A^2\sqrt{s}$
Maximum on-state voltage drop	V_{TM}	16 A, $T_J = 25\text{ }^{\circ}\text{C}$	1.25		V
On-state slope resistance	r_t	$T_J = 125\text{ }^{\circ}\text{C}$	12.0		$m\Omega$
Threshold voltage	$V_{T(TO)}$		1.0		V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$T_J = 25\text{ }^{\circ}\text{C}$	0.5		mA
		$T_J = 125\text{ }^{\circ}\text{C}$	10		
Holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$, $T_J = 25\text{ }^{\circ}\text{C}$	-	150	
Maximum latching current	I_L	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	200		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J\text{ max.}$, linear to 80 %, $V_{DRM} = R_g - k = \text{Open}$	500		$V/\mu s$
Maximum rate of rise of turned-on current	dI/dt		150		$A/\mu s$

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
Maximum peak gate power	P_{GM}		8.0		W
Maximum average gate power	$P_{G(AV)}$		2.0		
Maximum peak positive gate current	$+I_{GM}$		1.5		A
Maximum peak negative gate voltage	$-V_{GM}$		10		V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^{\circ}\text{C}$	60		mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	45		
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	20		
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^{\circ}\text{C}$	2.5		V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	2.0		
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	1.0		
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^{\circ}\text{C}$, $V_{DRM} = \text{Rated value}$	0.25		mA
Maximum DC gate current not to trigger	I_{GD}		2.0		

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^{\circ}\text{C}$	0.9		μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^{\circ}\text{C}$	4		
Typical turn-off time	t_q		110		



THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-40 to 125	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	2.5	°C/W
Maximum thermal resistance, junction to ambient	R_{thJA}		62	
Typical thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style TO-220AB FULL-PAK (94/V0)	25TTS08FP	
			25TTS12FP	

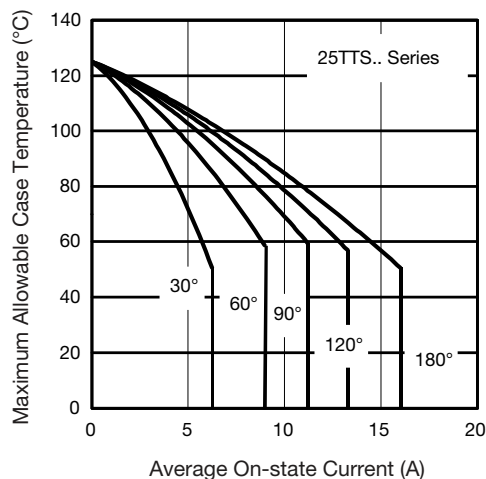


Fig. 1 - Current Rating Characteristics

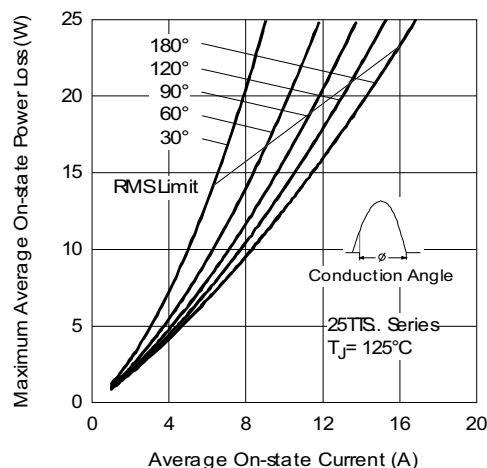


Fig. 3 - On-State Power Loss Characteristics

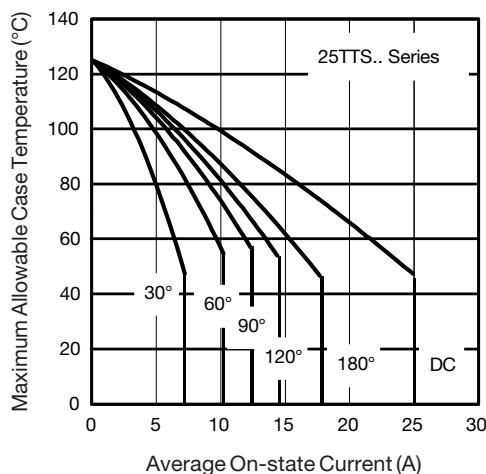


Fig. 2 - Current Rating Characteristics

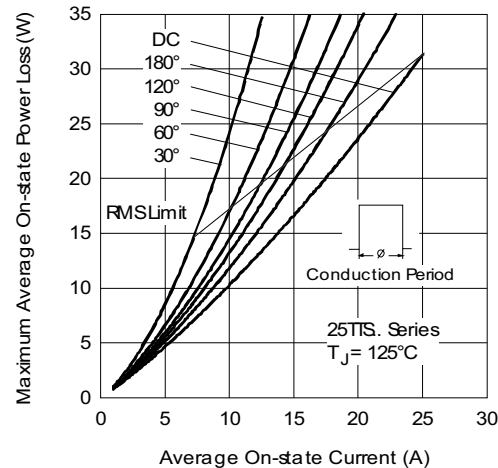


Fig. 4 - On-State Power Loss Characteristics

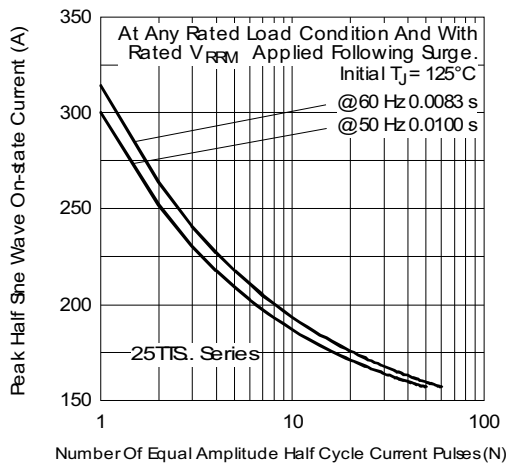


Fig. 5 - Maximum Non-Repetitive Surge Current

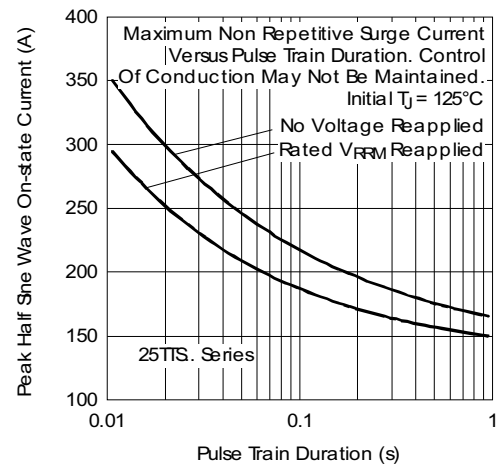


Fig. 6 - Maximum Non-Repetitive Surge Current

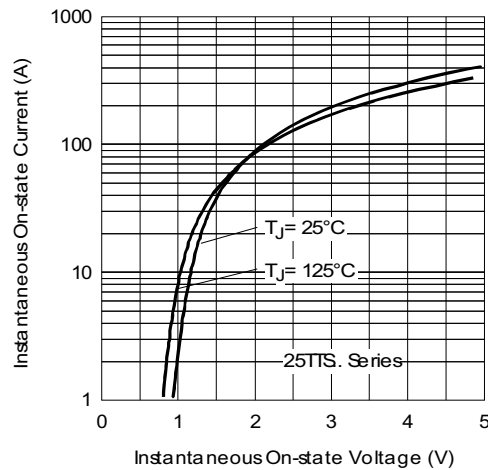


Fig. 7 - On-State Voltage Drop Characteristics

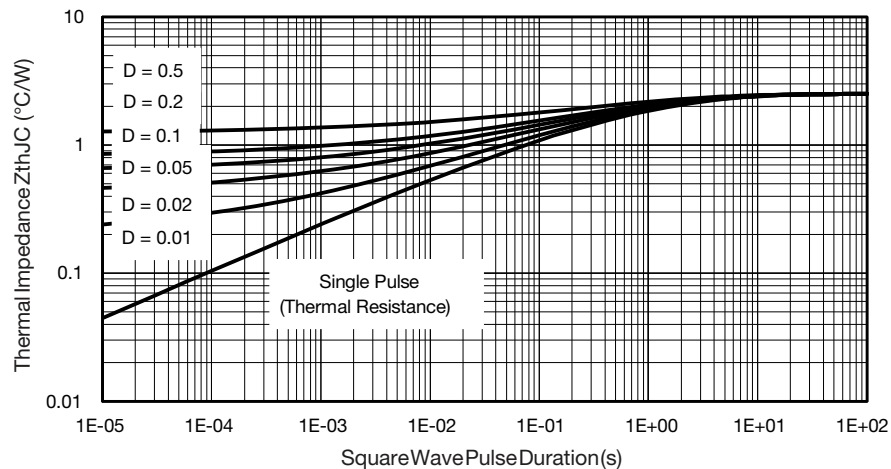


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

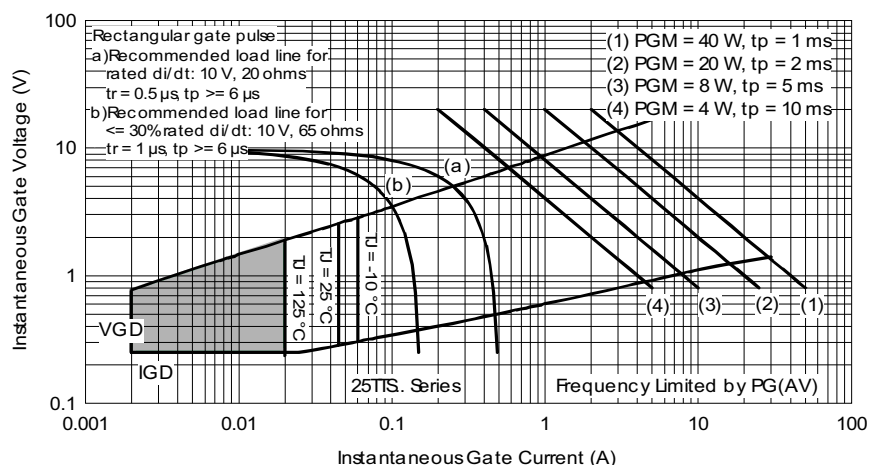


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	25	T	T	S	12	FP	PbF
	1	2	3	4	5	6	7	8

- 1 - Vishay Semiconductors product
- 2 - Current rating (25 = 25 A)
- 3 - Circuit configuration:
T = Single thyristor
- 4 - Package:
T = TO-220AB
- 5 - Type of silicon:
Standard recovery rectifier
- 6 - Voltage code x 100 = V_{RRM}
08 = 800 V
12 = 1200 V
- 7 - FULL-PAK
- 8 - Environmental digit:
PbF = Lead (Pb)-free and RoHS compliant
-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)

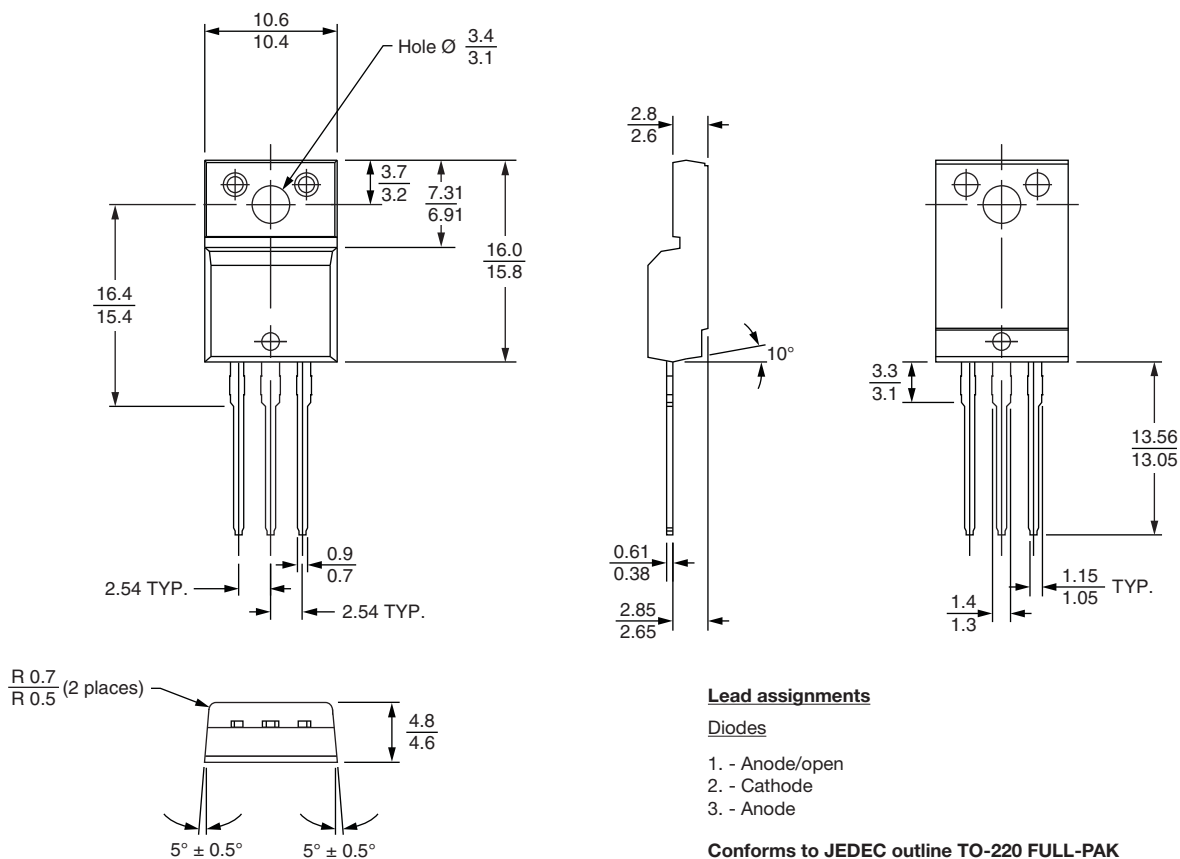
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-25TTS08FPPbF	50	1000	Antistatic plastic tubes
VS-25TTS08FP-M3	50	1000	Antistatic plastic tubes
VS-25TTS12FPPbF	50	1000	Antistatic plastic tubes
VS-25TTS12FP-M3	50	1000	Antistatic plastic tubes

LINKS TO RELATED DOCUMENTS

Dimensions		www.vishay.com/doc?95072
Part marking information	TO-220FP PbF	www.vishay.com/doc?95069
	TO-220FP -M3	www.vishay.com/doc?95456



DIMENSIONS in millimeters



Lead assignments

Diodes

1. - Anode/open
2. - Cathode
3. - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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